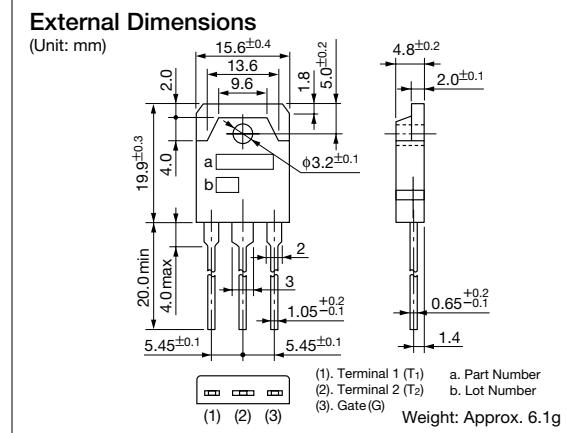


TO-3P 16A Triac

TM1641P-L(L), TM1661P-L(L)

■ Features

- Repetitive peak off-state voltage: $V_{DRM}=400, 600V$
- RMS on-state current: $I_{T(RMS)}=16A$
- Gate trigger current: $I_{GT}=30mA$ max (MODE I, II, III)



■ Absolute Maximum Ratings

Parameter	Symbol	Ratings		Unit	Conditions
		TM1641P-L(L)	TM1661P-L(L)		
Repetitive peak off-state voltage	V_{DRM}	400	600	V	
RMS on-state current	$I_{T(RMS)}$	16		A	Conduction angle 360°, $T_c=103^\circ C$
Surge on-state current	I_{TSM}	160		A	50Hz full-cycle sinewave, Peak value, Non-repetitive, $T_j=125^\circ C$
Peak gate voltage	V_{GM}	10		V	
Peak gate current	I_{GM}	2		A	
Peak gate power loss	P_{GM}	5		W	
Average gate power loss	$P_{G(AV)}$	0.5		W	
Junction temperature	T_j	-40 to +125		°C	
Storage temperature	T_{stg}	-40 to +125		°C	

■ Electrical Characteristics

($T_j=25^\circ C$, unless otherwise specified)

Parameter	Symbol	Ratings			Unit	Conditions
		min	typ	max		
Off-state current	I_{DRM}			2.0	mA	$V_D=V_{DRM}, R_{GK}=\infty, T_j=125^\circ C$
				0.1		$V_D=V_{DRM}, R_{GK}=\infty, T_j=25^\circ C$
On-state voltage	V_{TM}			1.6	V	Pulse test, $I_{TM}=20A$
Gate trigger voltage	V_{GT}	I	0.8	1.5	V	$V_D=6V, R_L=10\Omega, T_C=25^\circ C$
		II	0.7	1.5		
		III	0.8	1.5		
		IV	1.0			
Gate trigger current	I_{GT}	I	12	30	mA	$V_D=6V, R_L=10\Omega, T_C=25^\circ C$
		II	16	30		
		III	25	30		
		IV	70			
Gate non-trigger voltage	V_{GD}	0.2			V	$V_D=1/2 \times V_{DRM}, T_j=125^\circ C$
Holding current	I_H		25		mA	$V_D=6V$
Thermal resistance	R_{th}			1.2	°C/W	Junction to case